Form 1449 (Modified)

Information Disclosure
Statement By Applicant

(Use Several Sheets if Necessary)

Atty Docket No. Application No.:
NOVLP068/NVLS-2818
Applicant:
Koos et al.
Filing Date
October 20, 2003

1765

U.S. Patent and Publication Documents

Examiner			-			Sub-	Filing
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Foreign Patent or Published Foreign Patent Application

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Initial	No.	No.	Date	Patent Office	Class	class	Yes	No
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)	Atty Docket No. NOVLP068/NVLS-2818	Application No.: 10/690,084
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(Use Several Sheets if Necessary)	Filing Date October 20, 2003	Group 1765

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